



20V PNP LOW POWER TRANSISTOR IN SOT23

Features

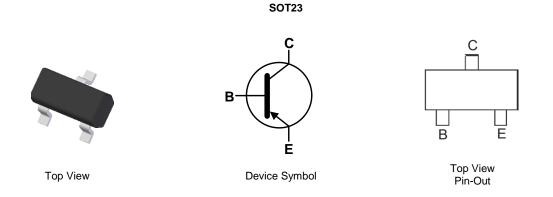
- BV_{CEO} > -20V
- BV_{ECO} > -7V
- I_C = -4A Continuous Collector Current
- V_{CE(sat)} < -55mV @ -1A
- R_{CE(sat)} = 34mΩ
- High Peak Current
- Complementary Part Number ZXTN25020CFH
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)

Applications

- MOSFET and IGBT Gate Driving
- DC-DC Converters



Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25020CFHTA	1B2	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

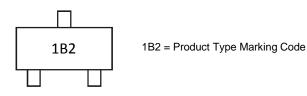
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



ZXTP25020CFH Document Number: DS33748 Rev. 4 - 2



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-25	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEO}	-20	V
Emitter-collector voltage (Reverse Blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current (Note 5)	Ic	-4	A
Base Current	IB	-1	A
Peak Pulse Current	I _{CM}	-10	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
	(Note 5)		0.73 5.84		
Power Dissipation	(Note 6)		1.05 8.4	W	
Linear derating factor	(Note 7)	P _D -	1.25 9.6		
	(Note 8)	-	1.81 14.5		
	(Note 5)		171		
Channel Desistance, lunction to Archient	(Note 6)		119	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	100	-C/vv	
	(Note 8)		69	1	
Fhermal Resistance, Junction to Lead	(Note 9)	R _{θJL}	74.95	°C/W	
Deerating and Storage Temperature Range	_	TJ. TSTG	-55 to +150	°C	

5. For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. Notes:

Same as note (5), except the device is surface mounted on 25mm x 25mm with 2 oz copper.
Same as note (5), except the device is surface mounted on 50mm x 50mm with 2 oz copper.

8. Same as note (7), except the device is measured at t<5secs.

9. Thermal resistance from junction to solder-point (at the end of the collector lead).

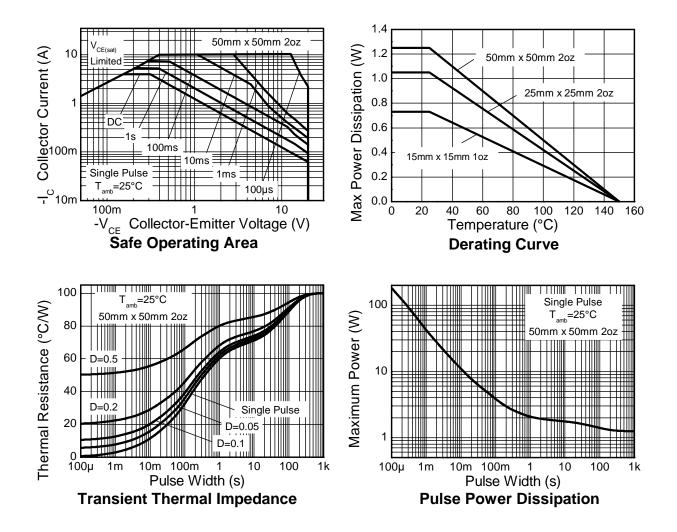
ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

10. Refer to JEDEC specification JESD22-A114 and JESD22-A115. Note:



Thermal Characteristics and Derating Information





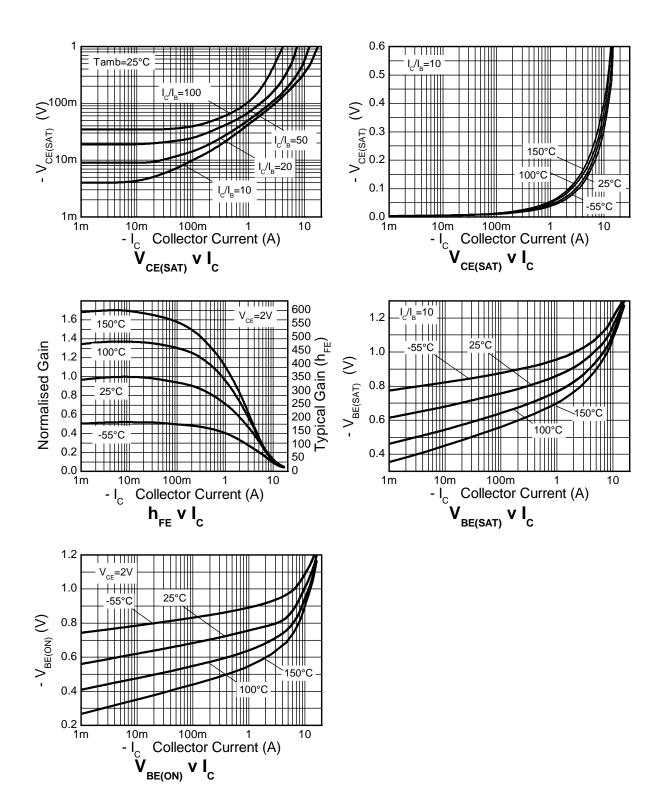
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-25	-50	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-20	-35	—	V	$I_{\rm C} = -10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.2	—	V	I _E = -100μA
Emitter-Base Breakdown Voltage	BV _{ECO}	-7	-8.8	—	V	I _E = -100μA
Collector-Base Cutoff Current	I _{СВО}	—	< -1	-50	nA	V _{CB} = -20V
Collector-Base Cutoff Current		_		-20	μA	$V_{CB} = -20V, T_{amb} = +100^{\circ}C$
Emitter-Base Cutoff Current	I _{EBO}	—	< -1	-50	nA	V _{EB} = -5.6V
		200	350	500		I _C = -10mA, V _{CE} = -2V
			250	_		I _C = -1A, V _{CE} = -2V
Static Forward Current Transfer Ratio (Note 11)	h _{FE}	_	140	—	—	I _C = -4A, V _{CE} = -2V
		_	40	—		I _C = -10A, V _{CE} = -2V
	V _{CE(sat)}	_	-43	-55	mV	I _C = -1A, I _B = -100mA
Collector Emitter Seturation Valage (Note 11)		_	-70	-100		I _C = -1A, I _B = -20mA
Collector-Emitter Saturation Voltage (Note 11)		—	-120	-170		$I_{\rm C} = -2A, I_{\rm B} = -40 {\rm mA}$
		_	-150	-210		I _C = -4A, I _B = -200mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	—	-930	-1050	mV	I _C = -4A, I _B = -200mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(on)}	—	-810	-900	mV	$I_{C} = -4A, V_{CE} = -2V$
Output Capacitance	C _{obo}	—	32.4	40	pF	$V_{CB} = -10V, f = 1MHz$
Transition Frequency	f _T	-	285	-	MHz	$V_{CE} = -10V, I_C = -50mA,$ f = 100MHz
Delay Time	t _(d)	—	38.4	—	nS	
Rise Time	t _(r)	—	49.2	—	nS	V _{CC} = -15V, I _C = -750mA,
Storage Time	t _(s)	—	168	—	nS	I _{B1} = -I _{B2} = -15mA
Fall Time	t _(f)	—	55	—	nS	

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 µs. Duty cycle \leq 2%.



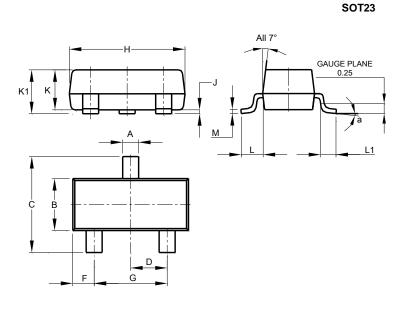
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

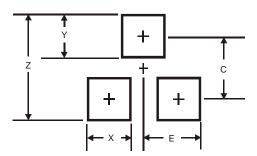
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
К	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	a 8°					
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



SOT23

Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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